

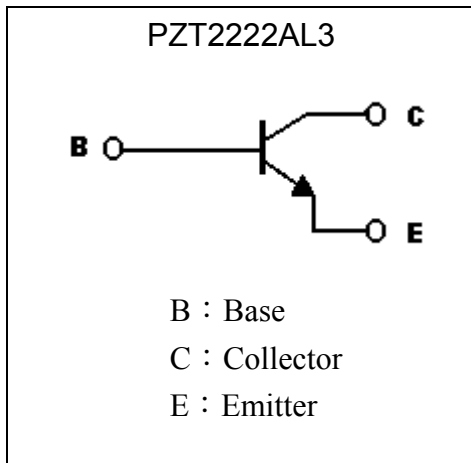
**General Purpose NPN Epitaxial Planar Transistor**

# PZT2222AL3

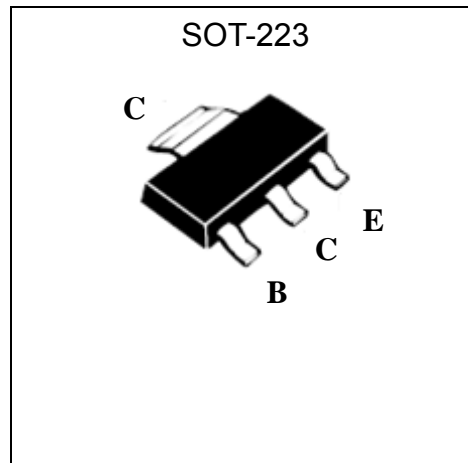
## Description

- The PZT2222AL3 is designed for using in driver stage of AF amplifier and general purpose switching application.
- High  $I_{C(Max)}$ ,  $I_{C(Max)} = 0.6A$ .
- Low  $V_{CE(sat)}$ , Typ.  $V_{CE(sat)} = 0.2V$  at  $I_C/I_B = 500mA/50mA$ .  
 Optimal for low Voltage operation.
- Complementary to BTA1036L3.

## Symbol

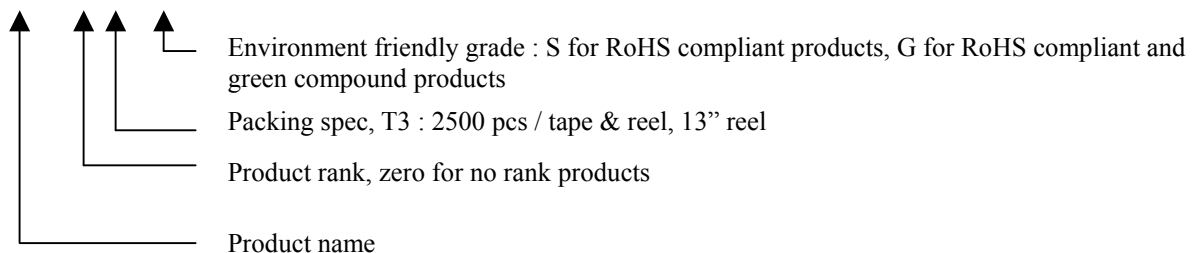


## Outline



## Ordering Information

Device	Package	Shipping
PZT2222AL3-0-T3-G	SOT-223 (Pb-free lead plating and halogen-free package)	2500 pcs / tape & reel



**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V <sub>CB0</sub>	75	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	I <sub>C</sub>	0.6	A
Power Dissipation (T <sub>C</sub> =25°C)	P <sub>D</sub>	5	W
Operating Junction and Storage Temperature Range	T <sub>j</sub> ; T <sub>stg</sub>	-55~+150	°C

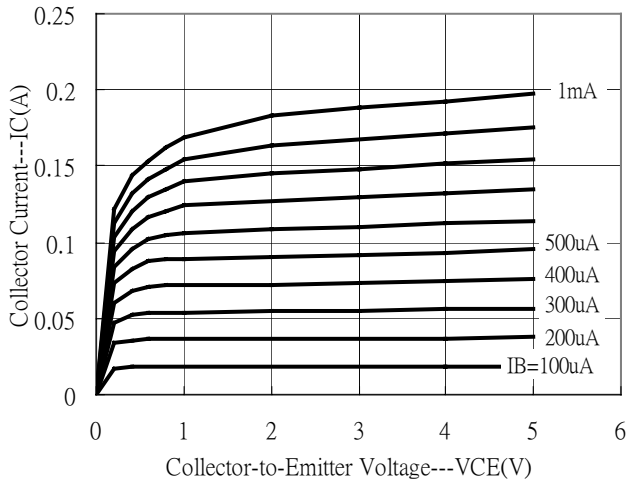
**Characteristics** (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	75	-	-	V	I <sub>C</sub> =10μA
BV <sub>CEO</sub>	50	-	-	V	I <sub>C</sub> =10mA
BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =10μA
I <sub>CB0</sub>	-	-	10	nA	V <sub>CB</sub> =60V
I <sub>CEX</sub>	-	-	10	nA	V <sub>CE</sub> =60V, V <sub>BE</sub> =-3V
I <sub>EBO</sub>	-	-	10	nA	V <sub>EB</sub> =3V
*V <sub>CE(sat)1</sub>	-	-	0.5	V	I <sub>C</sub> =380mA, I <sub>B</sub> =10mA
*V <sub>CE(sat)2</sub>	-	-	0.25	V	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA
*V <sub>CE(sat)3</sub>	-	0.2	0.45	V	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA
*V <sub>BE(sat)1</sub>	0.7	-	1.0	V	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA
*V <sub>BE(sat)2</sub>	-	-	1.2	V	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA
*h <sub>FE1</sub>	35	-	-		V <sub>CE</sub> =10V, I <sub>C</sub> =0.1mA
*h <sub>FE2</sub>	50	-	-		V <sub>CE</sub> =10V, I <sub>C</sub> =1mA
*h <sub>FE3</sub>	75	-	-		V <sub>CE</sub> =10V, I <sub>C</sub> =10mA
*h <sub>FE4</sub>	100	-	300		V <sub>CE</sub> =10V, I <sub>C</sub> =150mA
*h <sub>FE5</sub>	40	-	-		V <sub>CE</sub> =10V, I <sub>C</sub> =500mA
f <sub>T</sub>	-	230	-	MHz	V <sub>CE</sub> =5V, I <sub>C</sub> =20mA, f=100MHz
C <sub>ob</sub>	-	9.3	-	pF	V <sub>CB</sub> =5V, f=1MHz

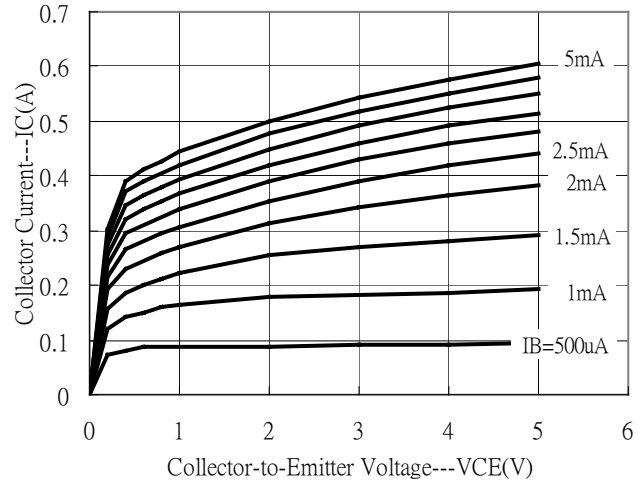
\*Pulse Test: Pulse Width ≤380μs, Duty Cycles≤2%

## Typical Characteristics

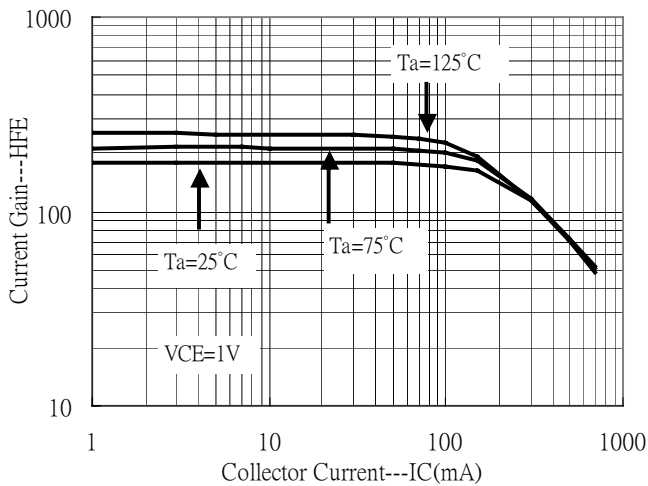
Emitter Grounded Output Characteristics



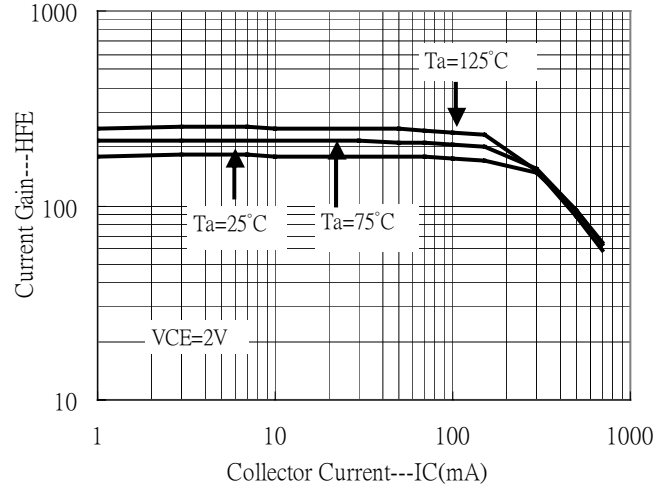
Emitter Grounded Output Characteristics



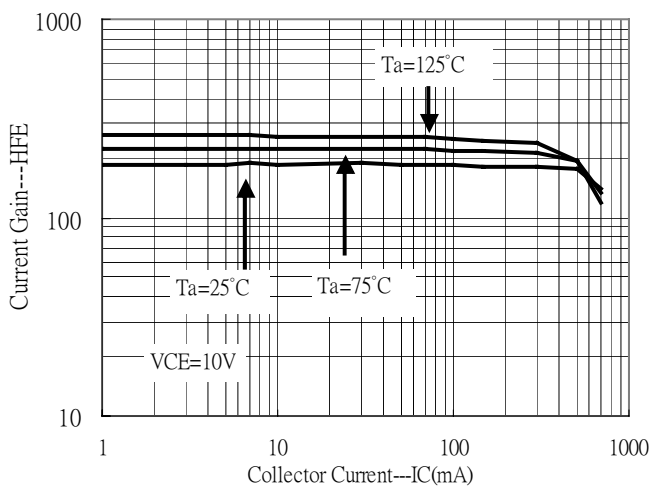
Current Gain vs Collector Current



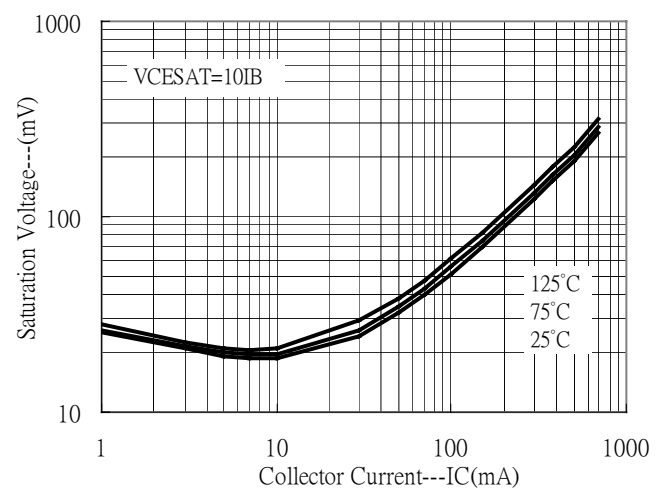
Current Gain vs Collector Current



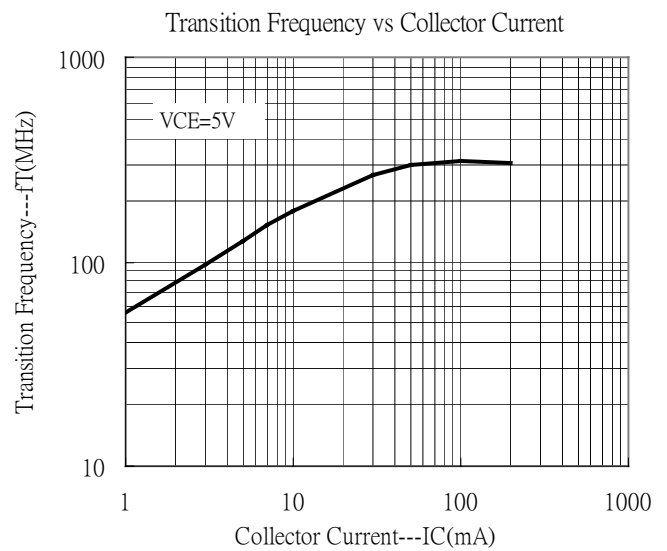
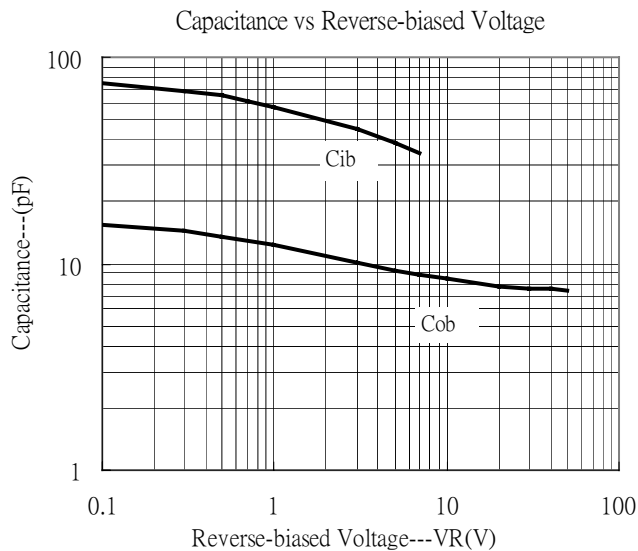
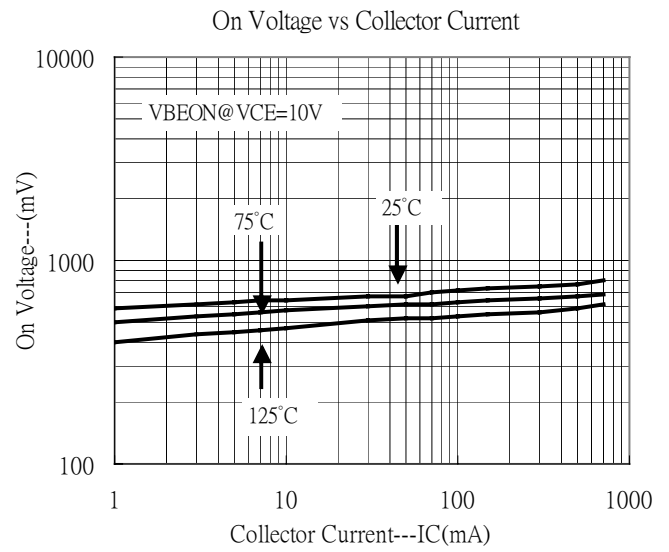
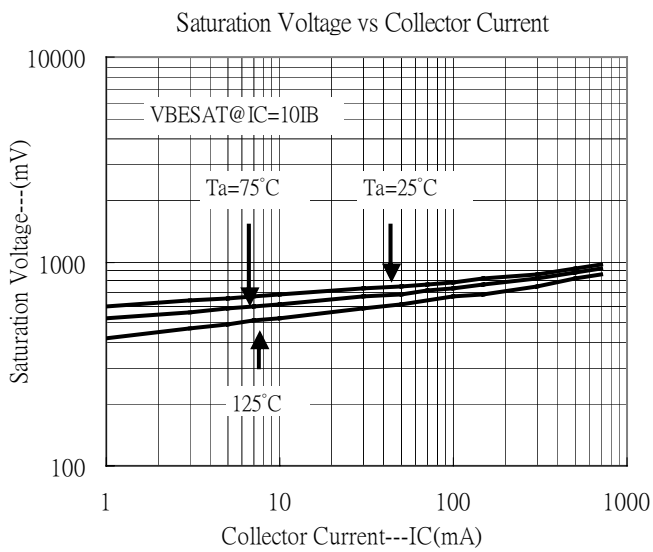
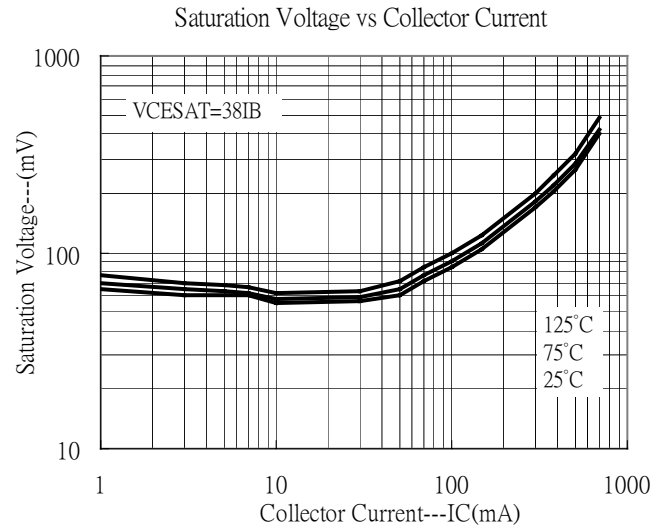
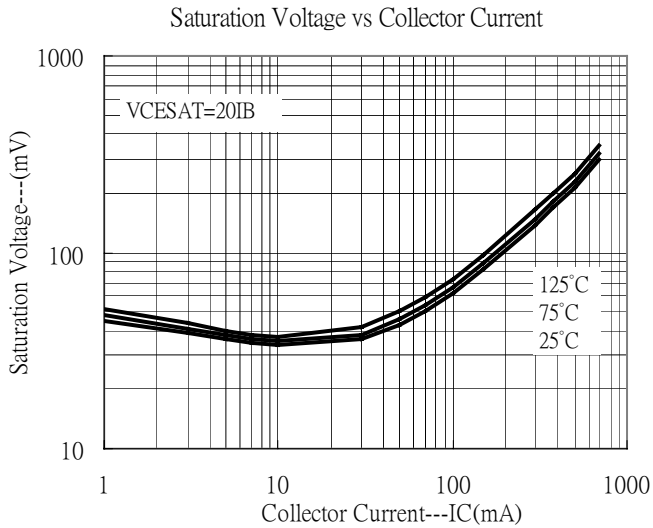
Current Gain vs Collector Current



Saturation Voltage vs Collector Current



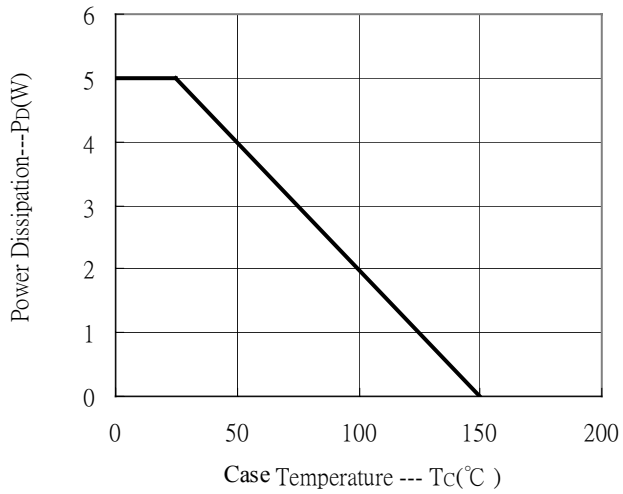
**Typical Characteristics(Cont.)**



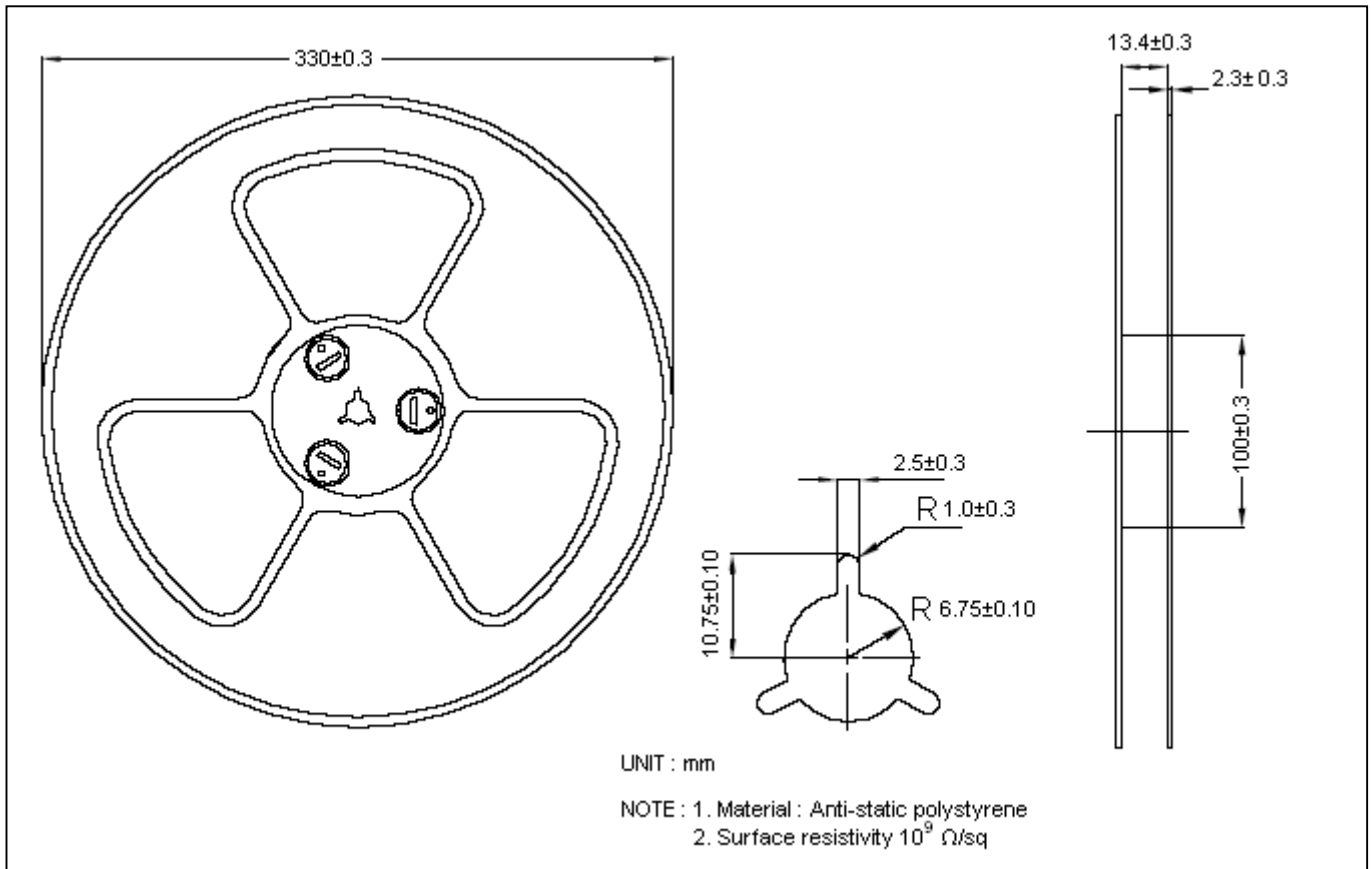


**Typical Characteristics(Cont.)**

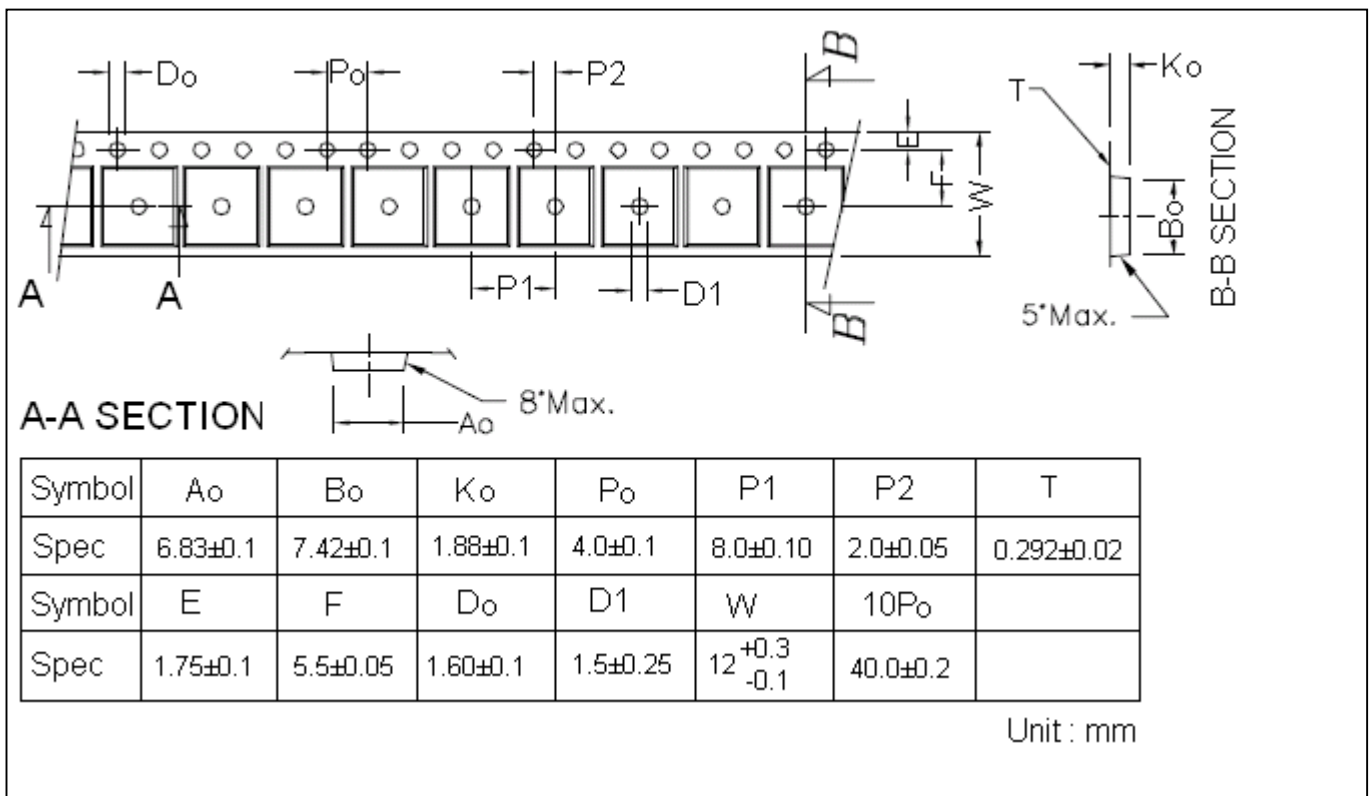
Power Derating Curve



**Reel Dimension**

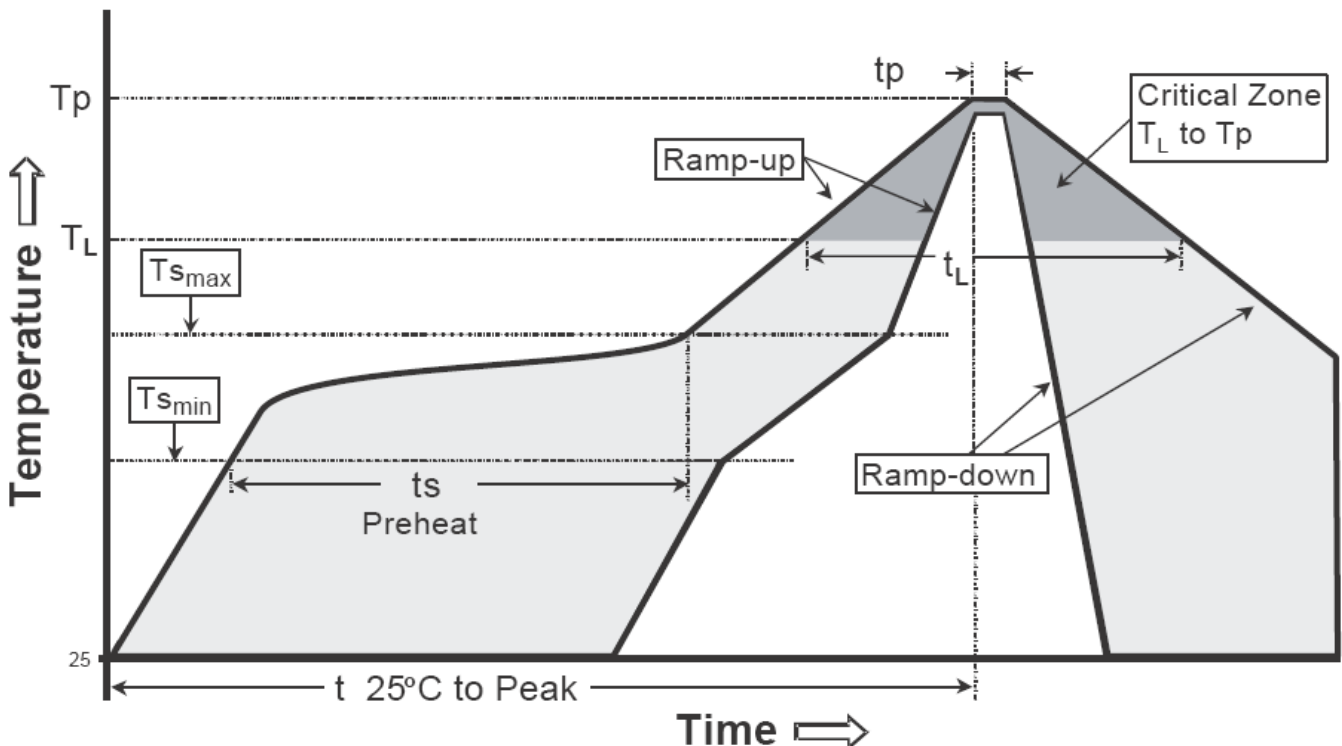


**Carrier Tape Dimension**



**Recommended wave soldering condition**

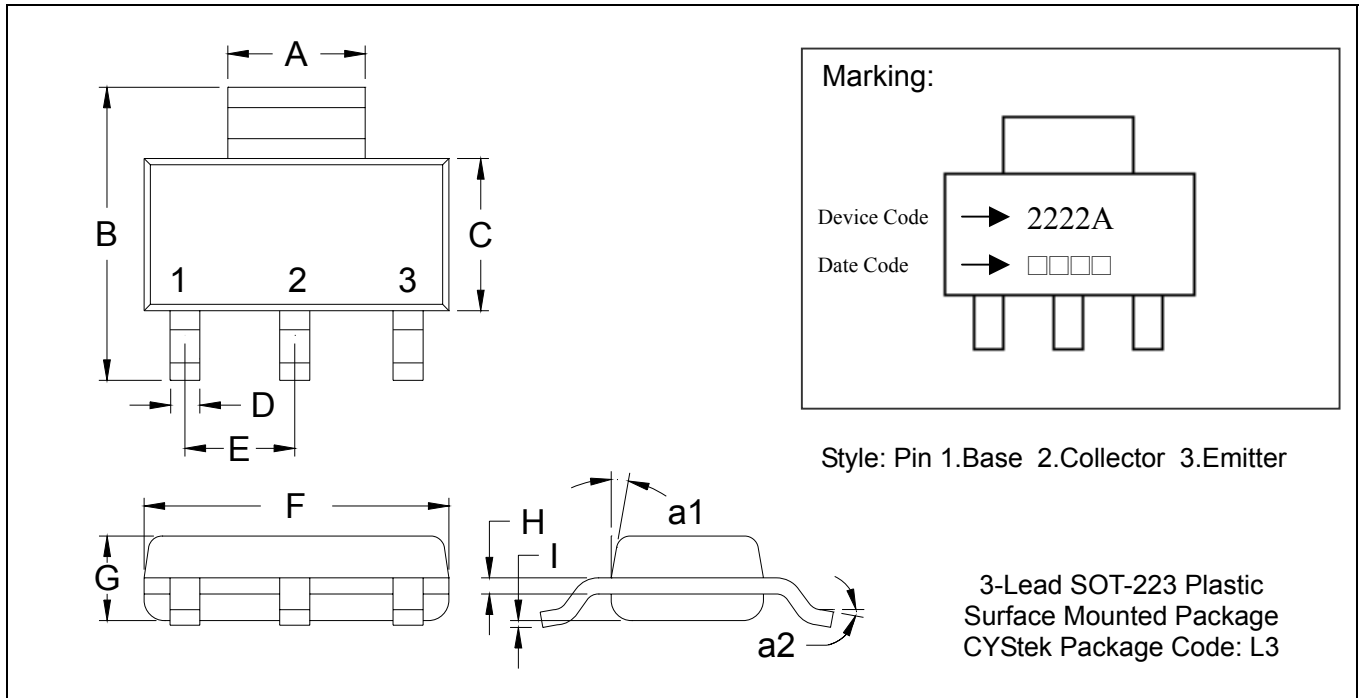
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

**Recommended temperature profile for IR reflow**


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tl)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-223 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					

- Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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